General purpose transistor (isolated transistor and diode) FML10

2SD2652 and a RB461F are housed independently in a UMT package.



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Transistors

Absolute maximum ratings (Ta=25°C)

Tr1

| Parameter | Symbol | Limits | Unit | |
|------------------------------|--------|-------------|------|--|
| Collector-base voltage | Vсво | 15 | V | |
| Collector-emitter voltage | VCEO | 12 | V | |
| Emitter-base voltage | Vebo | 6 | V | |
| | lc | 1.5 | Α | |
| Collector current | Іср | 3 | A * | |
| Power dissipation | Pc | 200 | mW | |
| Junction temperature | Tj | 150 | °C | |
| Range of storage temperature | Tstg | -40 to +125 | °C | |
| | | | | |

Di2

| Parameter | Symbol | Limits | Unit |
|---------------------------------------|--------|-------------|------|
| Reak reverse voltage | Vrm | 25 | V |
| Average rectified forward current | lf | 700 | mA |
| Forward current surge peak (60Hz, 1∞) | IFSM | 3 | A |
| Reverse voltage (DC) | Vr | 20 | V |
| Junction temperature | Tj | 125 | °C |
| Range of storage temperature | Tstg | -40 to +125 | °C |

•Electrical characteristics (Ta=25°C)

| Parameter | Symbo | l L | Limits | | Unit | | | |
|---|---------------------------------------|---|--|---------------------|--------------------------------|---------------------------------------|--|---|
| Collector-base voltage | Vсво | | 15 | | V | _ | | |
| Collector-emitter voltage | VCEO | | 12 | | V | _ | | |
| Emitter-base voltage | Vebo | | 6 | | V | _ | | |
| Collector current | lc | | | | А | | | |
| | Іср | | | | A × | ¢ | | |
| Power dissipation | Pc | | 200 | | mW | _ | | |
| Junction temperature | Tj | | 150 | | °C | | | |
| Range of storage temperature | Tstg | -40 | to +12 | 25 | °C | | | |
| Single pulse, Pw=1ms | | | | | | | | |
| Di2 | | | | | | | | |
| Parameter | 5 | Symbol | Liı | mits | ι | Init | | |
| Reak reverse voltage | everse voltage VRM | | 2 | 25 | | V | | |
| Average rectified forward current | | IF | 7 | 700 | n | nA | | |
| Forward current surge peak (60H | Forward current surge peak (60Hz, 1∞) | | 3 | | A | | | |
| Reverse voltage (DC) | everse voltage (DC) VR | | 20 | | V | | | 7 |
| Inction temperature Tj | | Ti | 125 | | °C | | | |
| Junction temperature | | , i | | 20 | | 9 | | |
| Range of storage temperature |) | Tstg | | io +12 | | 20 | | |
| Range of storage temperature Electrical characteristics (| (Ta=25°(| Tstg C) | -40 t | to +12 | 25 (| 2 C | 30 | |
| Range of storage temperature Electrical characteristics (Ir1 Parameter | (Ta=25°(| Tstg C) | -40 t | - | 25 (| °C Unit | Conditions | |
| Range of storage temperature Electrical characteristics (| (Ta=25°(| Tstg C) Symbol BVсво | -40 t Min. 15 | to +12 | 25 (| 2 C | Ic=10µА | |
| Range of storage temperature Electrical characteristics (Ir1 Parameter | (Ta=25°C | Tstg C) | -40 t | to +12 | 25 (| C C Unit V V | | |
| Range of storage temperature Electrical characteristics (Tr1 Parameter Collector-base breakdown voltation | (Ta=25°(s age l pltage / | Tstg C) Symbol BVсво | -40 t Min. 15 | Typ. | 25 (| C C Unit | Ic=10µА | |
| Range of storage temperature Electrical characteristics (Ir1 Parameter Collector-base breakdown volta Collector-emitter breakdown volta | (Ta=25°(s age l pltage / | Tstg C) Symbol BVceo BVceo | -40 t Min. 15 12 | Typ. - | 25 (| C C Unit V V | lc=10μA lc=1mA | |
| Range of storage temperature Electrical characteristics (Tr1 Parameter Collector-base breakdown volta Collector-emitter breakdown voltage | (Ta=25°(s age l pltage / | Tstg C) Symbol BVceo BVceo BVeeo | -40 t Min. 15 12 | Typ. - - | 25 (Max. | Unit V V | Ic=10μA Ic=1mA Iε=10μA | |
| Range of storage temperature Electrical characteristics (Ir1 Parameter Collector-base breakdown volta Collector-emitter breakdown volta Emitter-base breakdown volta Collector cutoff current | (Ta=25°(age I bitage I ge I | Tstg C) Symbol BVceo BVceo BVeeo Iceo | -40 t Min. 15 12 | Typ. - - | 25 C | Unit V V v | Ic=10µA Ic=1mA Ie=10µA Vcв=15V | |
| Range of storage temperature Electrical characteristics (Ir1 Parameter Collector-base breakdown volta Collector-emitter breakdown voltage Collector cutoff current Emitter cutoff current | (Ta=25°(age I bitage I ge I | Tstg C) Symbol. BVcBo BVcBo BVcBo ICBO IcBo | -40 t Min. 15 12 | Typ. - - - | Max. — — 100 100 | Unit V V v nA nA | Ic=10µA Ic=1mA IE=10µA Vcв=15V VEB=6V | * |
| Range of storage temperature Electrical characteristics (Ir1 Parameter Collector-base breakdown volta Collector-emitter breakdown voltage Collector cutoff current Emitter cutoff current Collector-emitter saturation vol | (Ta=25°(age I bitage I ge I | Tstg C) Symbol BVceo BVceo BVceo ICBO IcBO IcBO VCE(sat) | -40 t Min. 15 12 6 - - | Typ. - - - | Max. - 100 100 200 | Unit V V V nA nA mV | Ic=10µA Ic=1mA IE=10µA VcB=15V VEB=6V Ic/IB=500mA/25mA VcE/Ic=2V/200mA | ~ |

| DIZ | | | | | | |
|-----------------|--------|------|------|------|------|------------|
| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
| Forward voltage | VF | - | - | 490 | mV | I⊧=700mA |
| Reverse current | Ir | - | - | 200 | μA | Vr=20V |
| | | | | | | |

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